

Ultra-low Power Consumption LDO

"HM1152 Series

CMOS Voltage Regulator With ON/OFF Switch

500mA

HM1152 is ultra-low power consumption low dropout voltage regulator (LDO) manufactured in CMOS processes. It can deliver up to 500mA of current while consuming only 0.6 μ A of quiescent current. It consists of a reference voltage generator, an error amplifier, a current foldback circuit, and a phase compensation circuit plus a driver transistor. The HM1152 is designed specifically for applications where very-low I_Q is a critical parameter. This device maintains low quiescent current consumption even in dropout mode to further increase the battery life.

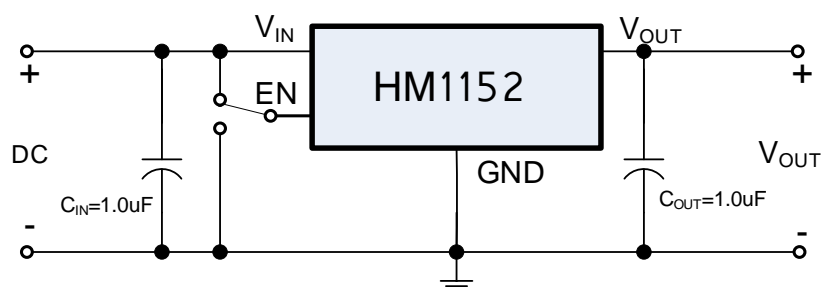
■ Features:

- Ultra-low Quiescent Current: 0.6 μ A
- Highly Accurate: $\pm 2\%$
- Dropout Voltage: 230mV@ $I_{OUT}=500$ mA
- Maximum Output Current: 500mA
- Input Voltage Range: 2.2V~7.0V
- Temperature Stability: ± 50 ppm/ $^{\circ}$ C
- ON/OFF Logic = Enable High
- Standby Current: 10nA
- C_{OUT} Discharge Circuit when EN Disable is Active
- Protections Circuits: Current Limiter, Short Circuit, Foldback
- Output Capacitor: Low ESR Ceramic Capacitor Compatible

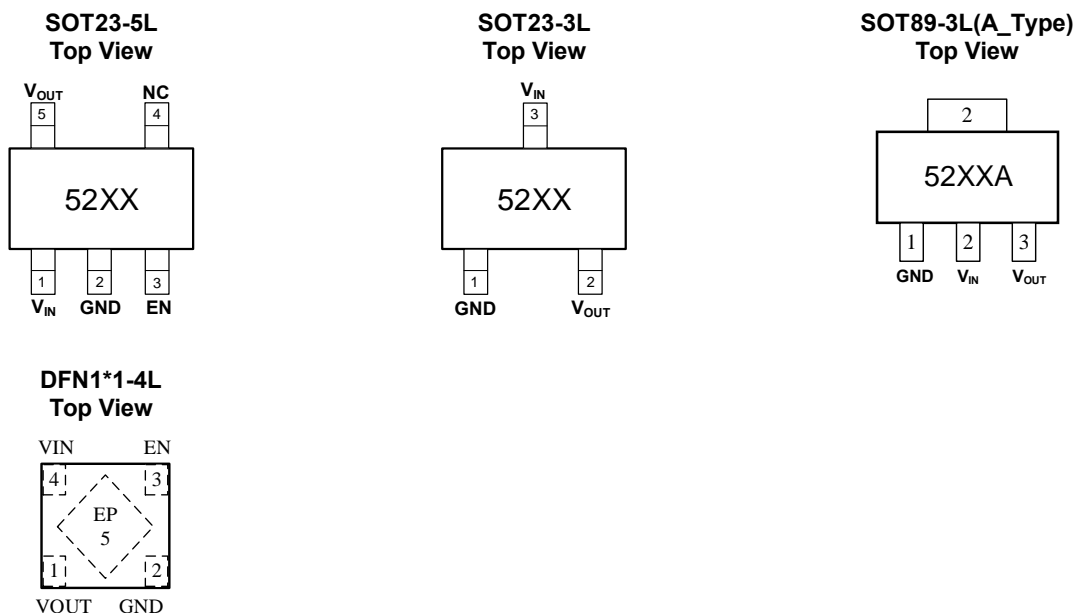
■ Applications:

- Smart wearer
- Long-life battery-powered devices
- Portable mobile devices, such as mobile phones, cameras, and so on
- Wireless communication equipment

■ Typical Applications:



Pin Configuration:



Product Selections:

Product Name	V _{OUT} (V)	Package	Ordering Name	Marking	Package Information
PT FFÍ GÓFGT Í	1.2	SOT23-5L	PT FFÍ GÓFGT Í	5212	Tape and Reel, 3000pcs
PT FFÍ GÓFÍ T Í	1.5	SOT23-5L	PT FFÍ GÓFÍ T Í	5215	
PT FFÍ GÓFÌ T Í	1.8	SOT23-5L	PT FFÍ GÓFÌ T Í	5218	
PT FFÍ GÓGFT Í	2.1	SOT23-5L	PT FFÍ GÓGFT Í	5221	
PT FFÍ GÓG T Í	2.5	SOT23-5L	PT FFÍ GÓG T Í	5225	
PT FFÍ GÓG T Í	2.8	SOT23-5L	PT FFÍ GÓG T Í	5228	
PT FFÍ GÓHET Í	3.0	SOT23-5L	PT FFÍ GÓHET Í	5230	
PT FFÍ GÓHHT Í	3.3	SOT23-5L	PT FFÍ GÓHHT Í	5233	
PT FFÍ GÓH T Í	3.6	SOT23-5L	PT FFÍ GÓH T Í	5236	
PT FFÍ GÓI ET Í	4.0	SOT23-5L	PT FFÍ GÓI ET Í	5240	
PT FFÍ GÓI ET Í	5.0	SOT23-5L	PT FFÍ GÓI ET Í	5250	
PT FFÍ GÓFGT Ü	1.2	SOT23-3L	PT FFÍ GÓFGT Ü	5212	
PT FFÍ GÓFÍ T Ü	1.5	SOT23-3L	PT FFÍ GÓFÍ T Ü	5215	
PT FFÍ GÓFÌ T Ü	1.8	SOT23-3L	PT FFÍ GÓFÌ T Ü	5218	
PT FFÍ GÓGFT Ü	2.1	SOT23-3L	PT FFÍ GÓGFT Ü	5221	
PT FFÍ GÓG T Ü	2.5	SOT23-3L	PT FFÍ GÓG T Ü	5225	
PT FFÍ GÓG T Ü	2.8	SOT23-3L	PT FFÍ GÓG T Ü	5228	
PT FFÍ GÓHET Ü	3.0	SOT23-3L	PT FFÍ GÓHET Ü	5230	
PT FFÍ GÓHHT Ü	3.3	SOT23-3L	PT FFÍ GÓHHT Ü	5233	
PT FFÍ GÓH T Ü	3.6	SOT23-3L	PT FFÍ GÓH T Ü	5236	
PT FFÍ GÓI ET Ü	4.0	SOT23-3L	PT FFÍ GÓI ET Ü	5240	
PT FFÍ GÓI ET Ü	5.0	SOT23-3L	PT FFÍ GÓI ET Ü	5250	
PT FFÍ GÓFGÜÜ	1.2	SOT89-3L	PT FFÍ GÓFGÜÜ	5212A	Tape and Reel, 1000pcs
PT FFÍ GÓFÍ ÜÜ	1.5	SOT89-3L	PT FFÍ GÓFÍ ÜÜ	5215A	
PT FFÍ GÓFÌ ÜÜ	1.8	SOT89-3L	PT FFÍ GÓFÌ ÜÜ	5218A	
PT FFÍ GÓGFÜÜ	2.1	SOT89-3L	PT FFÍ GÓGFÜÜ	5221A	

PT FFÍ GÓG ÚÜ	2.5	SOT89-3L	PT FFÍ GÓG ÚÜ	5225A	
PT FFÍ GÓG ÚÜ	2.8	SOT89-3L	PT FFÍ GÓG ÚÜ	5228A	
PT FFÍ GÓH ÚÜ	3.0	SOT89-3L	PT FFÍ GÓH ÚÜ	5230A	
PT FFÍ GÓH ÚÜ	3.3	SOT89-3L	PT FFÍ GÓH ÚÜ	5233A	
PT FFÍ GÓH ÚÜ	3.6	SOT89-3L	PT FFÍ GÓH ÚÜ	5236A	
PT FFÍ GÓE ÚÜ	4.0	SOT89-3L	PT FFÍ GÓE ÚÜ	5240A	
PT FFÍ GÓE ÚÜ	5.0	SOT89-3L	PT FFÍ GÓE ÚÜ	5250A	
PT FFÍ GÓG ÖÜ	1.2	DFN1*1-4L	PT FFÍ GÓG ÖÜ	5212	Tape and Reel, 10000pcs
PT FFÍ GÓF ÖÜ	1.5	DFN1*1-4L	PT FFÍ GÓF ÖÜ	5215	
PT FFÍ GÓF ÖÜ	1.8	DFN1*1-4L	PT FFÍ GÓF ÖÜ	5218	
PT FFÍ GÓG ÖÜ	2.1	DFN1*1-4L	PT FFÍ GÓG ÖÜ	5221	
PT FFÍ GÓG ÖÜ	2.5	DFN1*1-4L	PT FFÍ GÓG ÖÜ	5225	
PT FFÍ GÓG ÖÜ	2.8	DFN1*1-4L	PT FFÍ GÓG ÖÜ	5228	
PT FFÍ GÓH ÖÜ	3.0	DFN1*1-4L	PT FFÍ GÓH ÖÜ	5230	
PT FFÍ GÓH ÖÜ	3.3	DFN1*1-4L	PT FFÍ GÓH ÖÜ	5233	
PT FFÍ GÓH ÖÜ	3.6	DFN1*1-4L	PT FFÍ GÓH ÖÜ	5236	
PT FFÍ GÓE ÖÜ	4.0	DFN1*1-4L	PT FFÍ GÓE ÖÜ	5240	
PT FFÍ GÓE ÖÜ	5.0	DFN1*1-4L	PT FFÍ GÓE ÖÜ	5250	

■ **Absolute Maximum Ratings:** (Unless otherwise indicated: $T_a=25^{\circ}\text{C}$)

PARAMETER	SYMBOL	RATINGS		UNITS
Input Voltage	V _{IN}	-0.3 ~ 8		V
Output Voltage	V _{OUT}	V _{SS} -0.3 ~ V _{IN} +0.3V		
Power Dissipation	P _D	SOT23-5	250	mW
		SOT23-3	250	
		SOT89-3	1000	
		DFN1*1-4L	200	
Thermal Resistance	R _{θJB} ⁽¹⁾	SOT23-5	180	°C/W
		SOT23-3	200	
		SOT89-3	100	
		DFN1*1-4L	160	
Operating Ambient Temperature	T _{opr}	-40 ~ +85		°C
Storage Temperature	T _{stg}	-40 ~ +125		
ESD Protection	ESD HBM	6000		V

Note: Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device.

⁽¹⁾ Mounted on JEDEC standard 4layer (2s2p) PCB test board

■ **Notes on Use:**

Input Capacitor (C_{IN}): 1.0 μF above

Output Capacitor (C_{OUT}): 1.0 μF above

■ Electrical Characteristics:

HM1152 Series

(Unless otherwise indicated: $T_a=25^{\circ}\text{C}$)

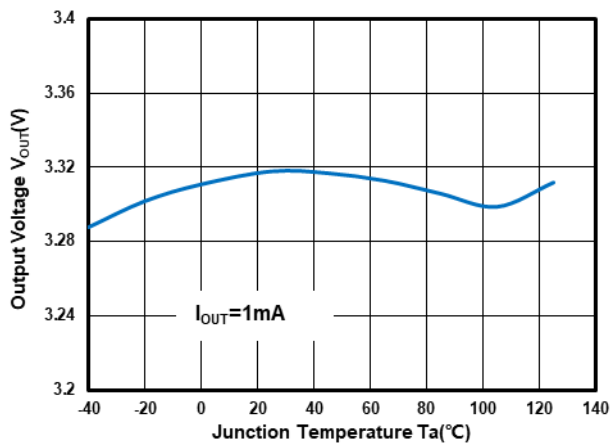
PARAMETER	SYMBOL	CONDITIONS	MIN.	TYP.	MAX.	UNIT
Output Voltage*1	$V_{\text{OUT(S)}}$	$V_{\text{IN}}=V_{\text{OUT(S)}}+2.0\text{V}$ $I_{\text{OUT}}=10\text{mA}$, $V_{\text{OUT(S)}}<2.0\text{V}$	$V_{\text{OUT(S)}}-0.03$	$V_{\text{OUT(S)}}$	$V_{\text{OUT(S)}}+0.03$	V
		$V_{\text{IN}}=V_{\text{OUT(S)}}+1.0\text{V}$ $I_{\text{OUT}}=10\text{mA}$, $V_{\text{OUT(S)}}\geq 2.0\text{V}$	$V_{\text{OUT(S)}}\times 0.98$		$V_{\text{OUT(S)}}\times 1.02$	
Dropout Voltage*2	V_{DROP}	$V_{\text{EN}}=V_{\text{IN}}$, $V_{\text{OUT}}<3\text{V}$ $I_{\text{OUT}}=500\text{mA}$		240		mV
		$V_{\text{EN}}=V_{\text{IN}}$, $V_{\text{OUT}}\geq 3\text{V}$ $I_{\text{OUT}}=500\text{mA}$		230		
Line Regulation	$\frac{\Delta V_{\text{OUT}}}{\Delta V_{\text{IN}} \cdot V_{\text{OUT(S)}}}$	$V_{\text{OUT(S)}}+0.5\text{V}\leq V_{\text{IN}}=V_{\text{EN}}\leq 7\text{V}$ $I_{\text{OUT}}=10\text{mA}$		0.05	0.1	%/V
Load Regulation	ΔV_{OUT2}	$V_{\text{IN}}=V_{\text{EN}}=V_{\text{OUT(S)}}+1.0\text{V}$ $1\text{mA}\leq I_{\text{OUT}}\leq 500\text{mA}$		50	90	mV
Temperature Stability	$\frac{\Delta V_{\text{OUT}}}{\Delta T_a \cdot V_{\text{OUT(S)}}}$	$V_{\text{IN}}=V_{\text{EN}}=V_{\text{OUT(S)}}+1.0\text{V}$ $I_{\text{OUT}}=1\text{mA}$ $-40^{\circ}\text{C}\leq T_a\leq 125^{\circ}\text{C}$		± 50		ppm/ $^{\circ}\text{C}$
GND Current ($V_{\text{EN}}=V_{\text{IN}}$)	I_{GND}	no load		0.6	0.9	μA
		$I_{\text{OUT}}=500\text{mA}$		210		μA
Shutdown Current ($V_{\text{EN}}=0$)	I_{SHUT}	$V_{\text{IN}}=7.0\text{V}$, $V_{\text{EN}}=0$		0.01	0.1	μA
Input Voltage	V_{IN}	---	2.2		7	V
Maximum Output Current	I_{OUTMAX}		450	500		mA
Current Limit*2	I_{LIM}	$V_{\text{IN}}=V_{\text{EN}}=V_{\text{OUT(S)}}+1.0\text{V}$ $V_{\text{OUT}} = 0.95 \times V_{\text{OUT(S)}}$		750		mA
Short Circuit Current	I_{SHORT}	$V_{\text{IN}}=V_{\text{EN}}=V_{\text{OUT(S)}}+1.0\text{V}$ $V_{\text{OUT}}=0\text{V}$		50		mA
C_{OUT} Auto Discharge	R_{DCHG}	$V_{\text{EN}}=0$, $V_{\text{OUT}}=V_{\text{OUT(S)}}$	280	450	640	Ω
Power Supply Rejection Ratio	PSRR	$f=10\text{Hz}$, $I_{\text{OUT}}=10\text{mA}$		64		dB
		$f=100\text{Hz}$, $I_{\text{OUT}}=10\text{mA}$		51		
		$f=1\text{kHz}$, $I_{\text{OUT}}=10\text{mA}$		34		
EN 'H' Level Voltage	V_{ENH}	---	1.0		7.0	V
EN 'L' Level Voltage	V_{ENL}	---	0		0.38	
EN 'H' Level Current	I_{ENH}	$V_{\text{IN}}=7.0\text{V}$, $V_{\text{EN}}=V_{\text{IN}}$	-0.1		0.1	μA
EN 'L' Level Current	I_{ENL}	$V_{\text{IN}}=7.0\text{V}$, $V_{\text{EN}}=0$	-0.1		0.1	

Notes:

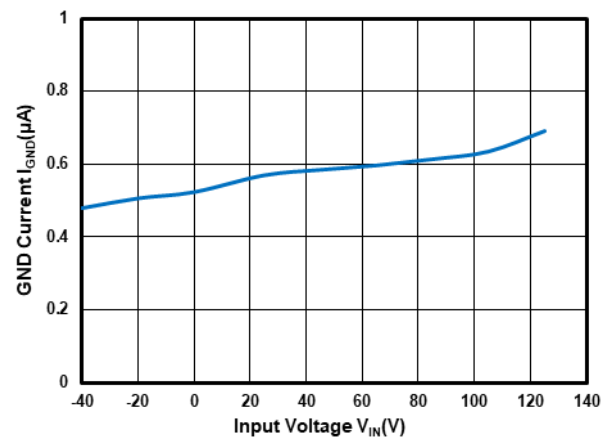
- $V_{\text{OUT(S)}}$: Output voltage when $V_{\text{IN}}=V_{\text{OUT}}+1\text{V}$, $I_{\text{OUT}}=1\text{mA}$.
- $V_{\text{DROP}}=V_{\text{IN1}} - (V_{\text{OUT(S)}}\times 0.98)$ where V_{IN1} is the input voltage when $V_{\text{OUT}} = V_{\text{OUT(S)}}\times 0.98$.
- I_{LIM} : Output current when $V_{\text{IN}}=V_{\text{OUT(S)}}+1\text{V}$ and $V_{\text{OUT}} = 0.95\times V_{\text{OUT(S)}}$.

■ Typical Performance Characteristics:

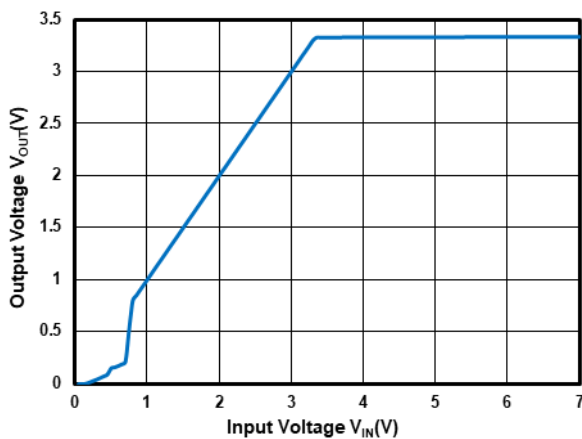
Test Conditions: $V_{IN}=V_{OUT}+1.0V$, $C_{IN}=1.0\mu F$, $C_{OUT}=1.0\mu F$, $T_a=25^\circ C$, unless otherwise indicated.



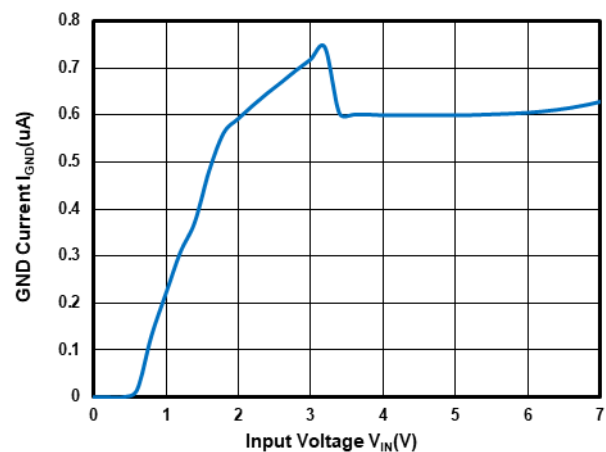
Output Voltage vs. Temperature at $V_{OUT}=3.3V$



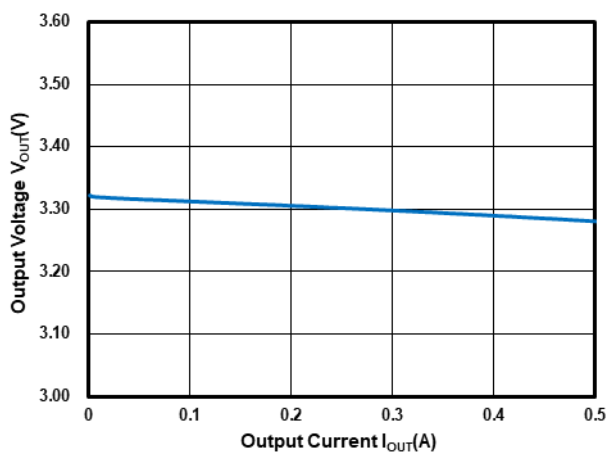
GND Current vs. Temperature at $V_{OUT}=3.3V$



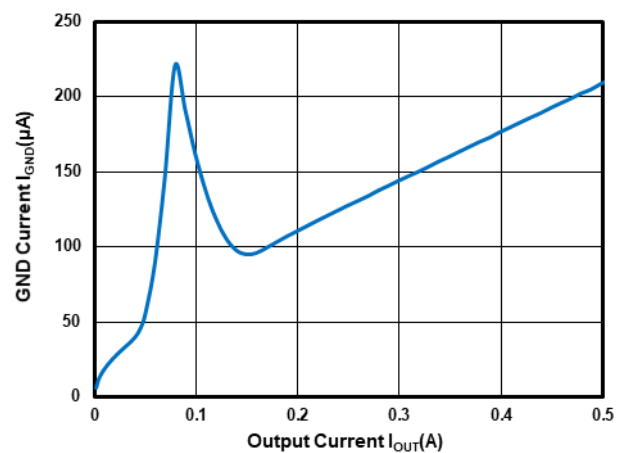
Output Voltage vs. Input Voltage at $V_{OUT}=3.3V$



GND Current vs. Input Voltage at $V_{OUT}=3.3V$



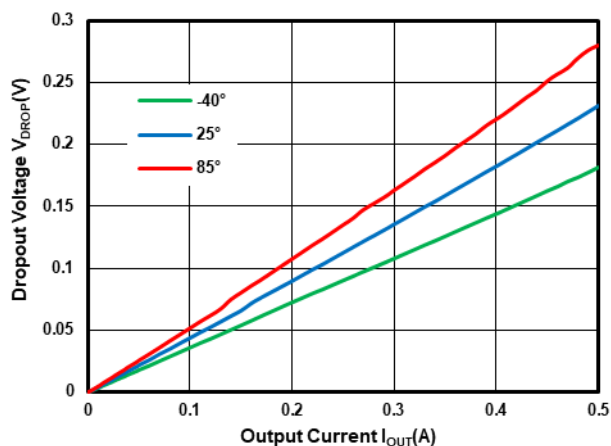
Output Voltage vs Output Current at $V_{OUT}=3.3V$



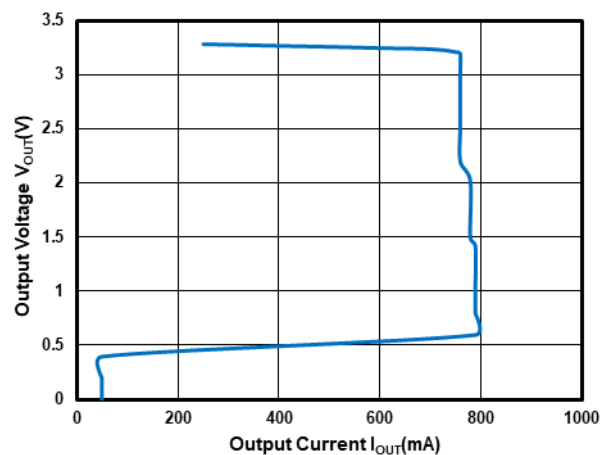
GND Current vs Output Current at $V_{OUT}=3.3V$

■ Typical Performance Characteristics (Continued):

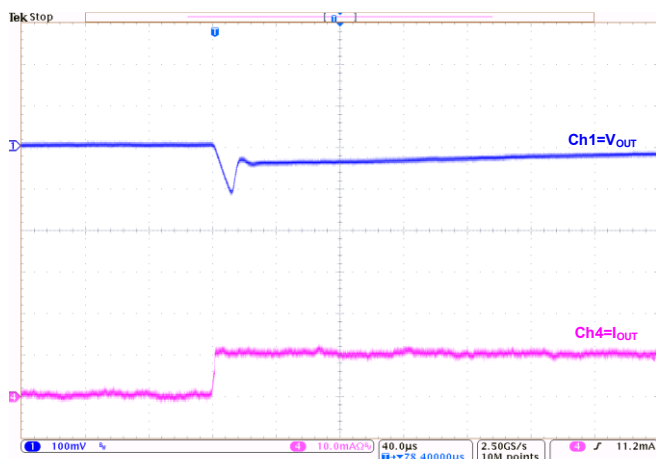
Test Conditions: $V_{IN}=V_{OUT}+1.0V$, $C_{IN}=1.0\mu F$, $C_{OUT}=1.0\mu F$, $T_a=25^\circ C$, unless otherwise indicated.



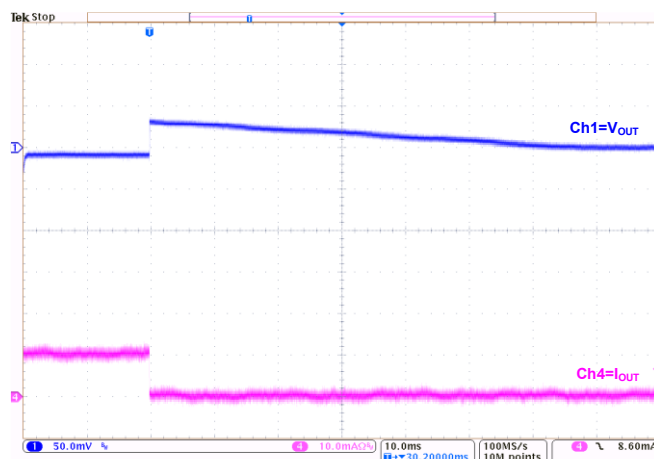
Dropout Voltage vs. Output Current at $V_{OUT}=3.3V$



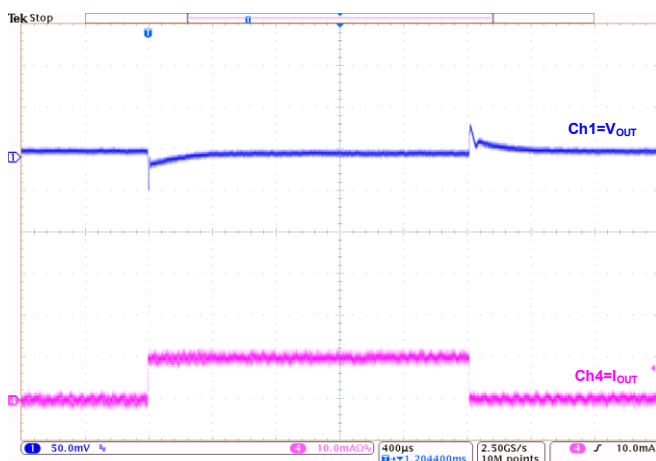
Output Current Fold-back at $V_{OUT}=3.3V$



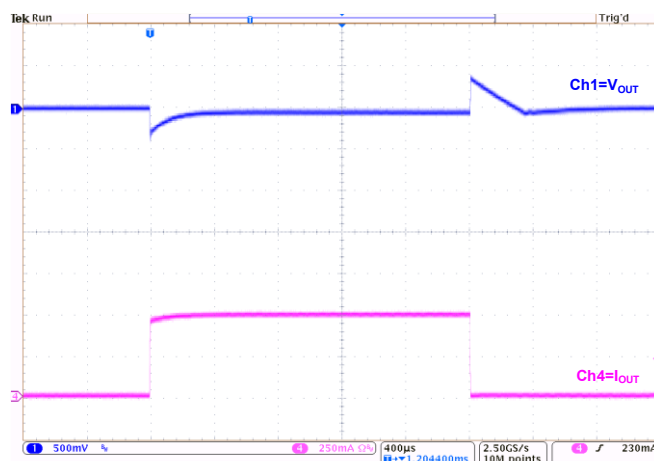
Load Transient at $V_{OUT}=3.3V$:
($I_{OUT}=0mA \sim 10mA$)



Load Transient at $V_{OUT}=3.3V$:
($I_{OUT}=10mA \sim 0mA$)



Load Transient at $V_{OUT}=3.3V$:
($I_{OUT}=1mA \sim 10mA \sim 1mA$)



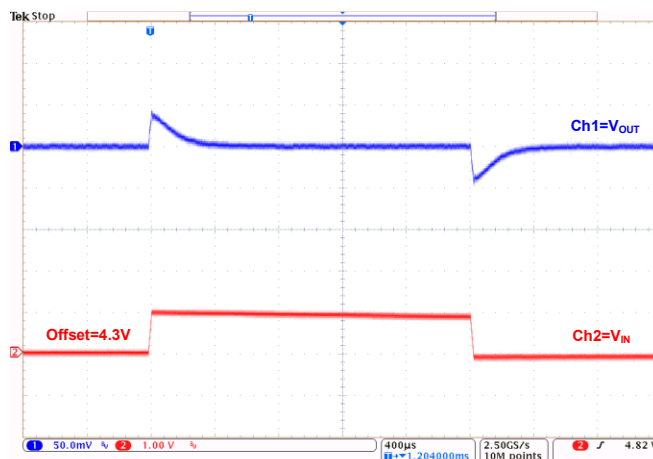
Load Transient at $V_{OUT}=3.3V$:
($I_{OUT}=1mA \sim 500mA \sim 1mA$)

■ Typical Performance Characteristics (Continued):

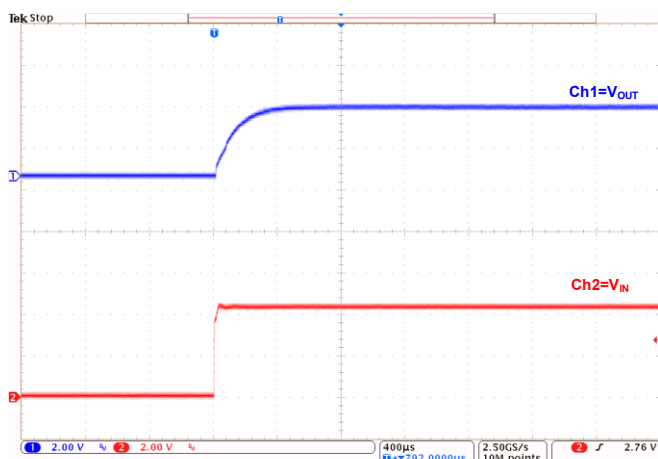
Test Conditions: $V_{IN}=V_{OUT}+1.0V$, $C_{IN}=1.0\mu F$, $C_{OUT}=1.0\mu F$, $T_a=25^\circ C$, unless otherwise indicated.



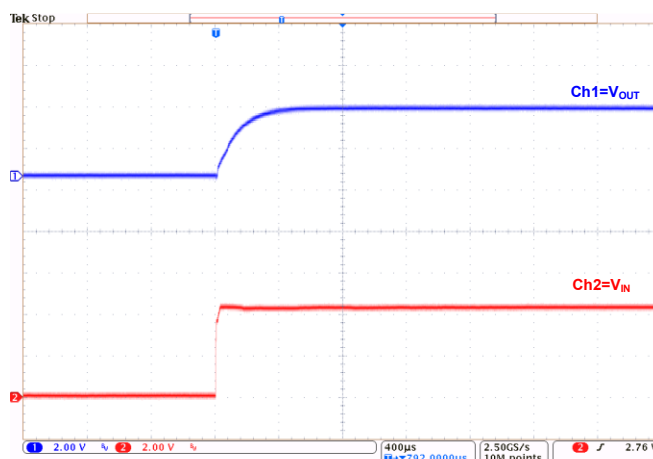
Line Transient at $V_{OUT}=3.3V$:
($I_{OUT}=1mA$)



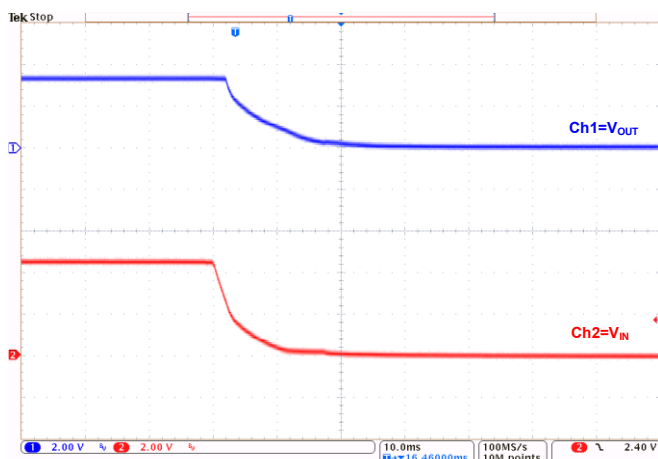
Line Transient at $V_{OUT}=3.3V$:
($I_{OUT}=10mA$)



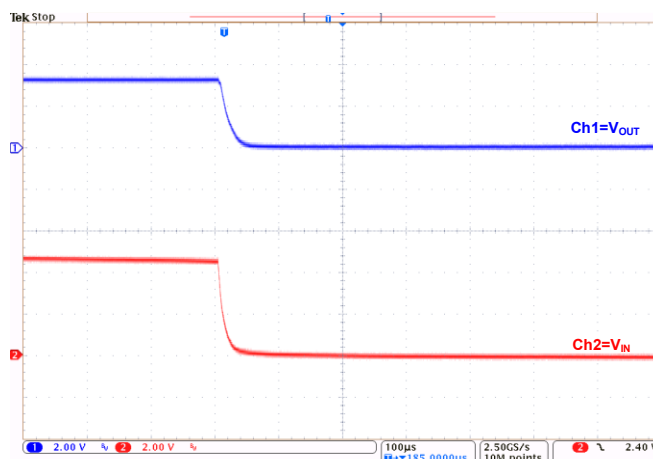
Power Up at $V_{OUT}=3.3V$:
($I_{OUT}=1mA$)



Power Up at $V_{OUT}=3.3V$:
($I_{OUT}=500mA$)



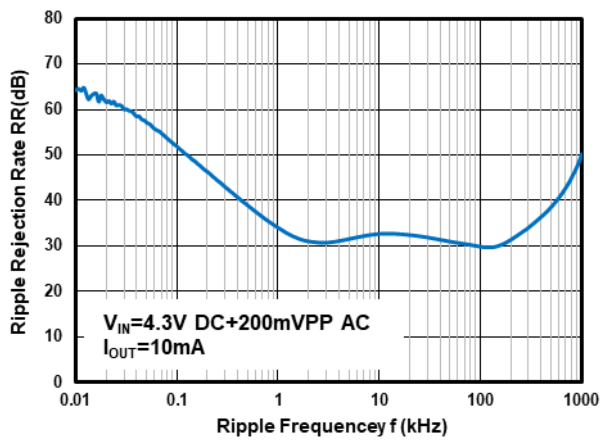
Power Down at $V_{OUT}=3.3V$:
($I_{OUT}=1mA$)



Power Down at $V_{OUT}=3.3V$:
($I_{OUT}=500mA$)

■ Typical Performance Characteristics (Continued):

Test Conditions: $V_{IN}=V_{OUT}+1.0V$, $C_{IN}=1.0\mu F$, $C_{OUT}=1.0\mu F$, $T_a=25^\circ C$, unless otherwise indicated.

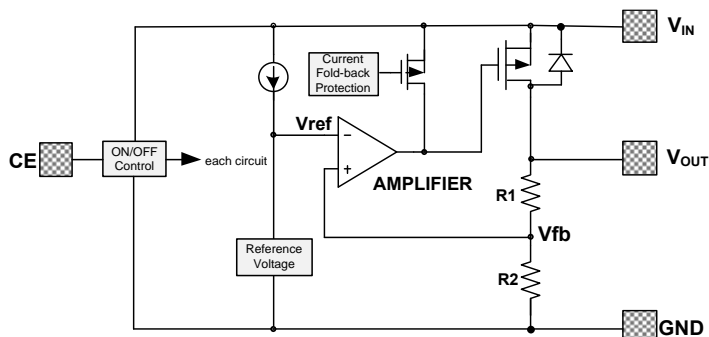


Power Supply Rejection Ratio at $V_{OUT}=3.3V$

■ Operational Explanation:

1. Output voltage control

The voltage divided by resistors R1 and R2 is compared with the internal reference voltage by the error amplifier. The amplifier output then drives the P-channel MOSFET connected to the V_{OUT} pin. The output voltage at the V_{OUT} pin is regulated by this negative feedback system. The current limit circuit and short protect circuit operate in relation to output current level. Further, the IC's internal circuitry can be in operation or shutdown modes controlled by the EN pin's signal.



2. Pass transistor

The pass transistor with low turn-on resistance used in PT FFÍ G is a P-channel MOSFET. If the potential on V_{OUT} pin is higher than V_{IN}, it is possible that IC will be destroyed due to reverse current which is caused by parasitic diodes between V_{IN} and V_{OUT}. Therefore, the V_{OUT} pin potential exceeds V_{IN}+0.3V is not allowed.

3. Current foldback and short circuit protection

The HM1152 series includes a combination of a fixed current limiter circuit and a foldback circuit, which aid the operations of the current limiter and circuit protection. When the load current reaches the current limit level, the fixed current limiter circuit operates and output voltage drops. As a result of this drop in output voltage, the foldback circuit operates, output voltage drops further and output current decreases. The short circuit current is about 65mA (typical value). This design can prevent the chip be damaged due to over temperature, moreover, the heat dissipation is limited by the package type.

Special attention should be paid to that the product of the dropout voltage on the chip and the output current must be smaller than the heat dissipation.

4. C_{OUT} Auto-Discharge Function

The HM1152 series can quickly discharge the electric charge at the output capacitor (C_{OUT}), when a low signal is set to the EN pin, which puts the whole IC into OFF state. The discharge function is achieved by an internal switch located between the V_{OUT} pin and the GND pin. In this state, the application is protected from a glitch operation caused by the electric charge at the output capacitor (C_{OUT}).

Moreover, discharge time of the output capacitor (C_{OUT}) is set by the C_{OUT} auto-discharge resistance (R_{DCHG}) and the output capacitor (C_{OUT}). By setting time constant of a C_{OUT} auto-discharge resistance value (R_{DCHG}) and an output capacitor value (C_{OUT}) as $\tau(\tau = C_{OUT} \times R_{DCHG})$, the output voltage after discharge via the internal switch is calculated by the following formulas.

$$V = V_{OUT(S)} \times e^{-t/\tau} \text{ or } t = \tau \ln(V_{OUT(S)} / V)$$

V: Output voltage after discharge

V_{OUT(S)}: Output voltage

t: Discharge time

$$\tau: C_{OUT} \times R_{DCHG}$$

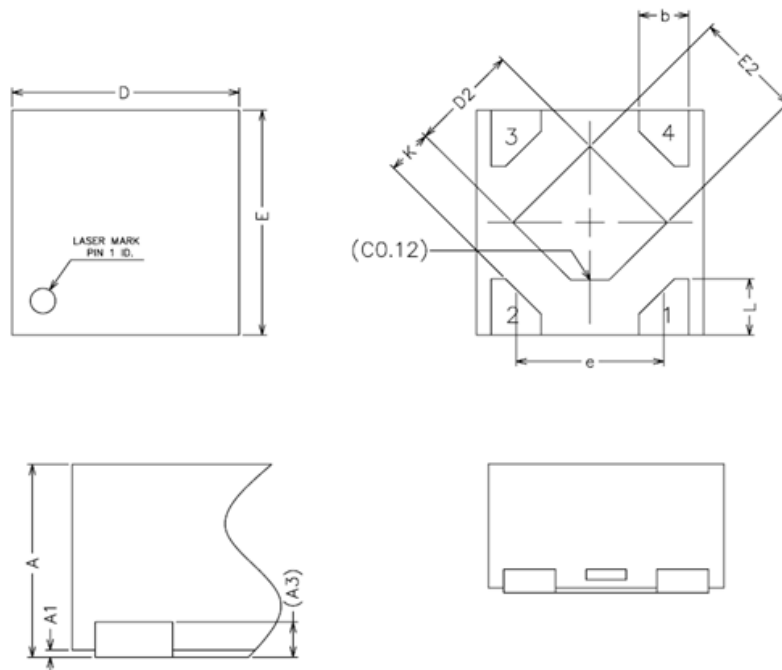
Please also note R_{DCHG} is depended on V_{IN} and When V_{IN} is high, R_{DCHG} is low.

■ **Notes:**

1. The input and output capacitors should be placed as close as possible to the IC.
2. If the impedance of the power supply is high, which is caused by forgetting installing input capacitor or installing too small value capacitor, the oscillation may occur.
3. Pay attention to the operation conditions of input and output voltage and load current, such that the power consumption in the IC should not exceed the allowable power consumption of the package even though the chip has short circuit protection.
4. IC has a built-in anti-static protection (ESD) circuit, but please do not add excessive stress to the IC.

■ Packaging Information:

DFN(1*1)-4L PACKAGE OUTLINE DIMENSIONS

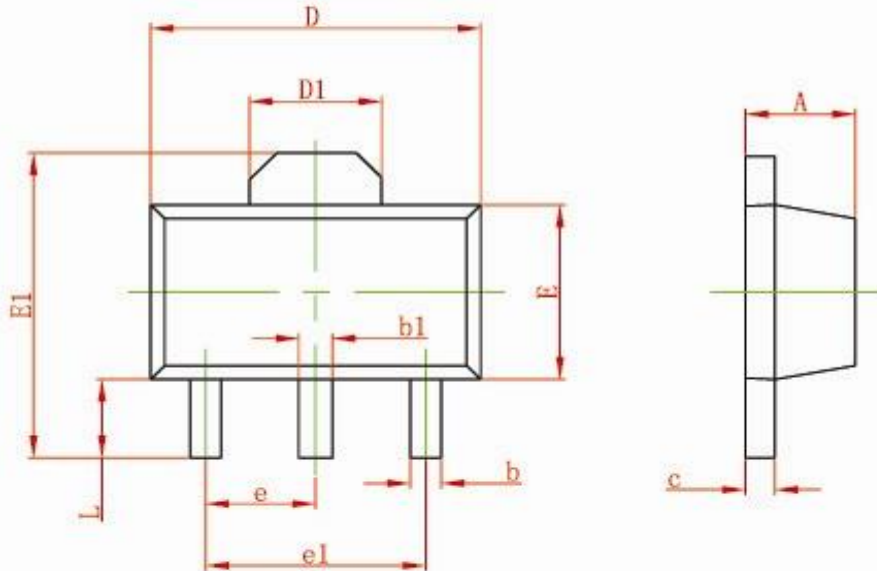


COMMON DIMENSIONS
 (UNITS OF MEASURE=MILLIMETER)

SYMBOL	MIN	NOM	MAX
A	0.50	0.55	0.60
A1	0.00	0.02	0.05
A3		0.100REF	
b	0.17	0.22	0.27
D	0.95	1.00	1.05
E	0.95	1.00	1.05
D2	0.43	0.48	0.53
E2	0.43	0.48	0.53
L	0.20	0.25	0.30
e	0.60	0.65	0.70
K	0.15	—	—

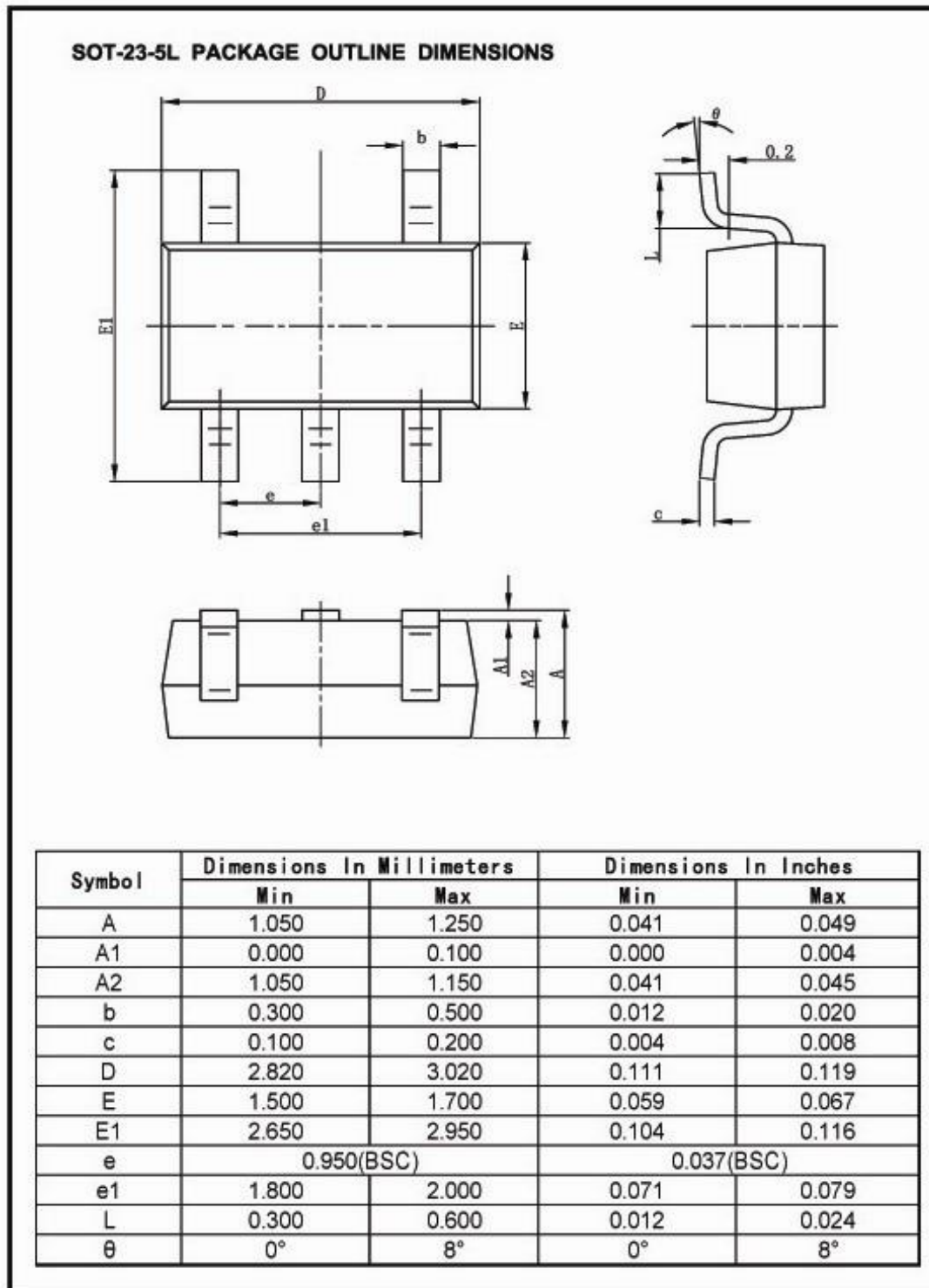
■ PACKAGING INFORMATION(Continued):

SOT-89-3L PACKAGE OUTLINE DIMENSIONS



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.400	1.600	0.055	0.063
b	0.320	0.520	0.013	0.197
b1	0.400	0.580	0.016	0.023
c	0.350	0.440	0.014	0.017
D	4.400	4.600	0.173	0.181
D1	1.550 REF		0.061 REF	
E	2.300	2.600	0.091	0.102
E1	3.940	4.250	0.155	0.167
e	1.500 TYP		0.060TYP	
e1	3.000 TYP		0.118TYP	
L	0.900	1.200	0.035	0.047

■ PACKAGING INFORMATION(Continued):



■ PACKAGING INFORMATION(Continued):

